

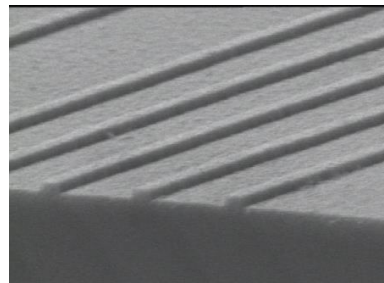
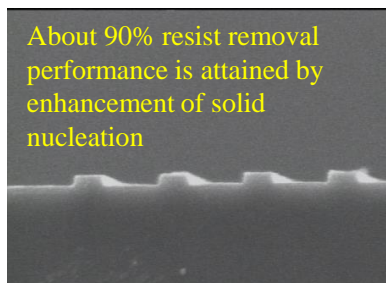
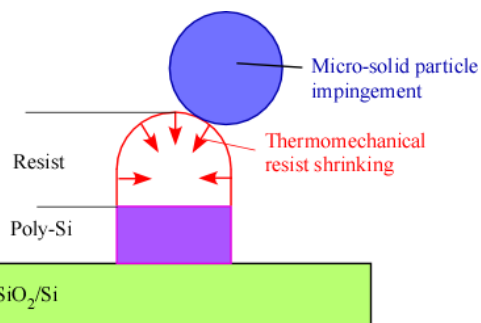
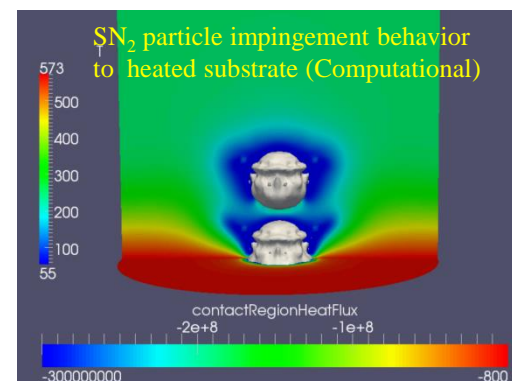
Jun Ishimoto, Daisuke Tan, U. Oh, Tomihiro Kubota, and Seiji Samukawa,

[Integrated Experimental and Numerical Study, of Thermomechanical Resist Removal-Cleaning Performance Using Cryogenic Micro-Solid Nitrogen Spray](#), *ECS Transactions*, Vol. 41, No.5, pp. 83-90 (2011).

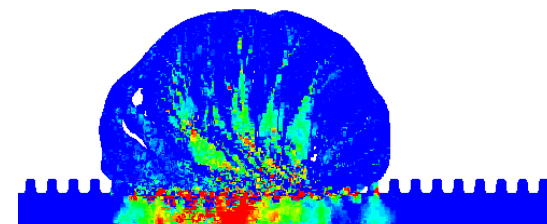
International collaboration: Hanyang Univ., Korea (Prof. Jin-Goo Park, NEMPL),
Northeastern Univ. (Prof. Ahmed A. Busnaina, NSEC)

Objectives:

- To develop wafer resist removal and cleaning technology using **micro-nano solid nitrogen spray (SN₂)** which becomes applicable to the special **device whose plasma damage becomes serious problem**, and applicable to the device that the **reactivity of the O₂ radical is high** such as **CCD or photovoltaic passive device**.
- New physical wafer resist removal and cleaning technology which is **not** required O₂ plasma or UV ashing. Chemical free, damage-less cleaning system should be developed.



90% resist removal performance has been achieved by micro-nano SN₂ spray cleaning without use of plasma ashing



Stress profile while SN₂ particle impingement to resist (Computational)

The magnitude of pressure in SN₂ particle and wafer resist increases with SN₂ impingement and fragmentation.